



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



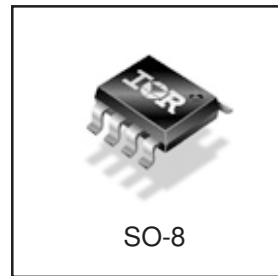
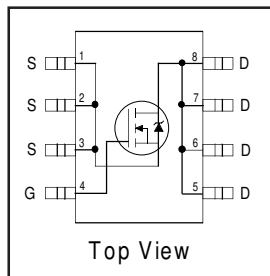
**Applications**

- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Computer Processor Power

<b>V<sub>DSS</sub></b>	<b>R<sub>DS(on)</sub> max(mΩ)</b>	<b>I<sub>D</sub></b>
<b>30V</b>	<b>12.5@V<sub>GS</sub> = 10V</b>	<b>11A</b>

**Benefits**

- Ultra-Low Gate Impedance
- Very Low R<sub>DS(on)</sub>
- Fully Characterized Avalanche Voltage and Current



**Absolute Maximum Ratings**

Symbol	Parameter	Max.	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-to-Source Voltage	± 20	V
I <sub>D</sub> @ T <sub>A</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	11	A
I <sub>D</sub> @ T <sub>A</sub> = 70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	9.0	
I <sub>DM</sub>	Pulsed Drain Current <sup>①</sup>	90	
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Maximum Power Dissipation <sup>③</sup>	2.5	W
P <sub>D</sub> @ T <sub>A</sub> = 70°C	Maximum Power Dissipation <sup>③</sup>	1.6	W
	Linear Derating Factor	0.02	mW/°C
T <sub>J</sub> , T <sub>STG</sub>	Junction and Storage Temperature Range	-55 to + 150	°C

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
R <sub>θJL</sub>	Junction-to-Drain Lead	—	20	°C/W
R <sub>θJA</sub>	Junction-to-Ambient <sup>④</sup>	—	50	

Notes <sup>①</sup> through <sup>④</sup> are on page 8  
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## Static @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.028	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	9.8	12.5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 11A ③
		—	13	17		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 8.8A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.0	—	3.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	20	μA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
		—	—	100		V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	200	nA	V <sub>GS</sub> = 16V
	Gate-to-Source Reverse Leakage	—	—	-200		V <sub>GS</sub> = -16V

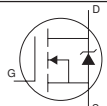
## Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)

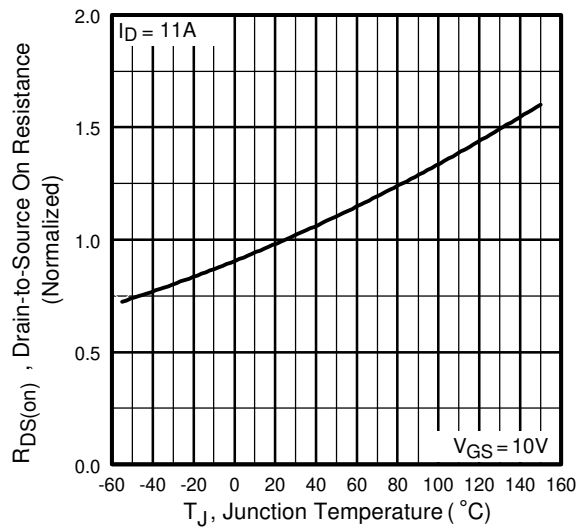
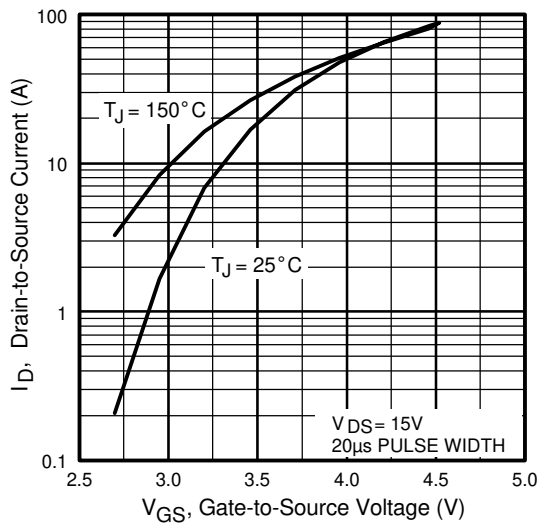
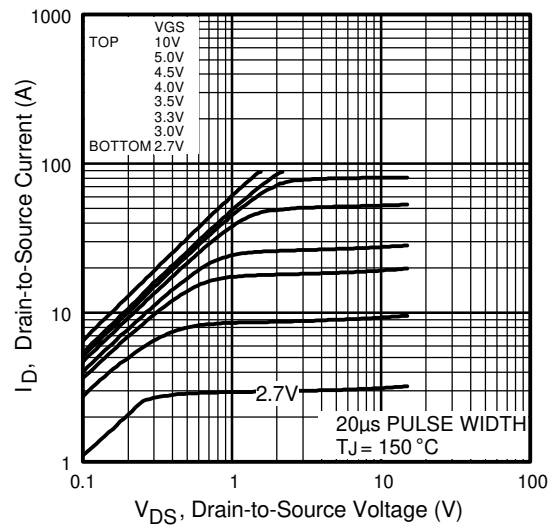
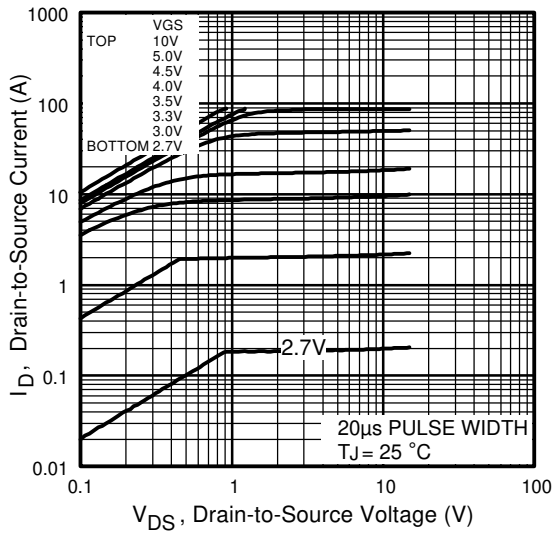
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g <sub>fs</sub>	Forward Transconductance	22	—	—	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 8.8A
Q <sub>g</sub>	Total Gate Charge	—	16	23	nC	I <sub>D</sub> = 8.8A
Q <sub>gs</sub>	Gate-to-Source Charge	—	7.4	11		V <sub>DS</sub> = 15V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	5.3	8.0		V <sub>GS</sub> = 4.5V ③
Q <sub>oss</sub>	Output Gate Charge	—	19	29		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 15V
t <sub>d(on)</sub>	Turn-On Delay Time	—	10	—	ns	V <sub>DD</sub> = 15V
t <sub>r</sub>	Rise Time	—	2.8	—		I <sub>D</sub> = 8.8A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	13	—		R <sub>G</sub> = 1.8Ω
t <sub>f</sub>	Fall Time	—	3.6	—		V <sub>GS</sub> = 4.5V ③
C <sub>iss</sub>	Input Capacitance	—	2100	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	710	—		V <sub>DS</sub> = 15V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	52	—		f = 1.0MHz

## Avalanche Characteristics

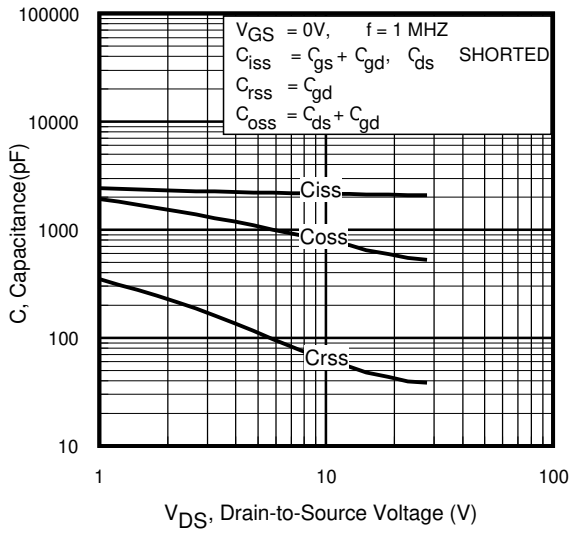
Symbol	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy②	—	230	mJ
I <sub>AR</sub>	Avalanche Current①	—	8.8	A

## Diode Characteristics

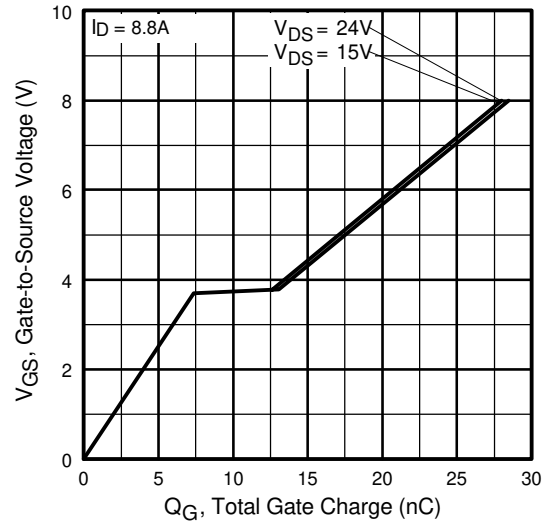
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	90		
V <sub>SD</sub>	Diode Forward Voltage	—	0.8	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 8.8A, V <sub>GS</sub> = 0V ③
		—	0.66	—		T <sub>J</sub> = 125°C, I <sub>S</sub> = 8.8A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	42	63	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 8.8A, V <sub>R</sub> = 15V
Q <sub>rr</sub>	Reverse Recovery Charge	—	59	89	nC	di/dt = 100A/μs ③
t <sub>rr</sub>	Reverse Recovery Time	—	42	63	ns	T <sub>J</sub> = 125°C, I <sub>F</sub> = 8.8A, V <sub>R</sub> = 15V
Q <sub>rr</sub>	Reverse Recovery Charge	—	61	92	nC	di/dt = 100A/μs ③



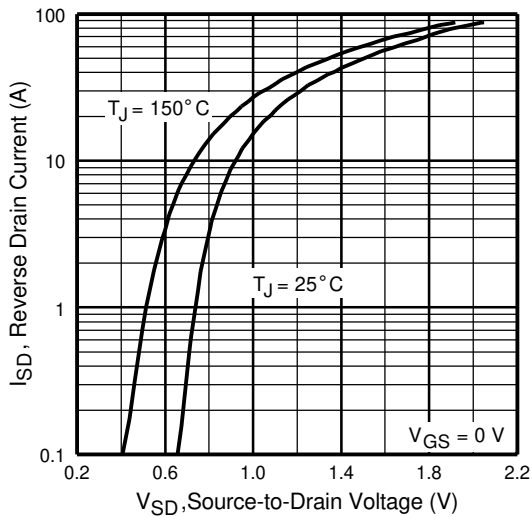




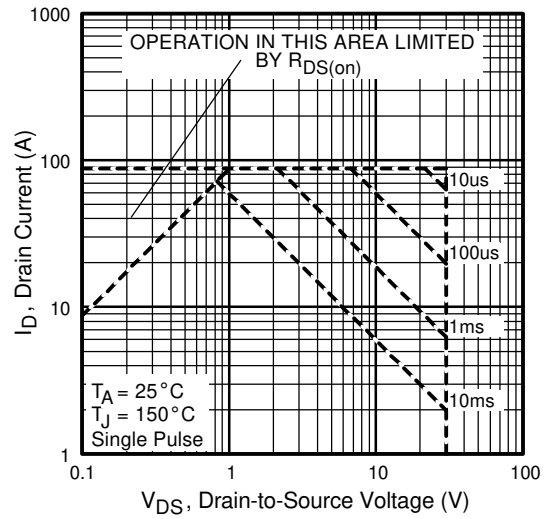
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage

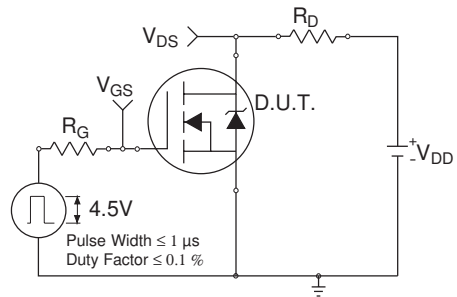
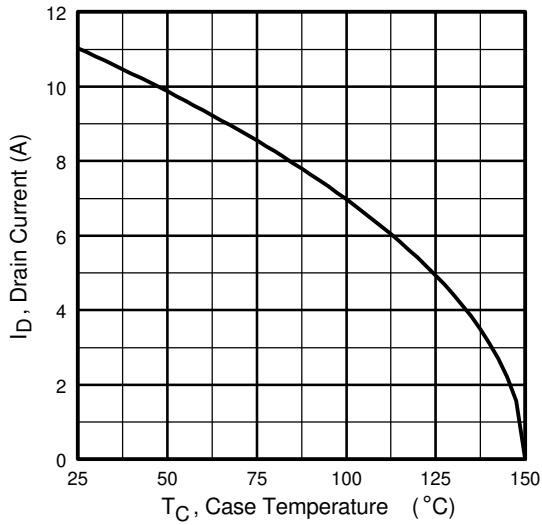


**Fig 7.** Typical Source-Drain Diode Forward Voltage

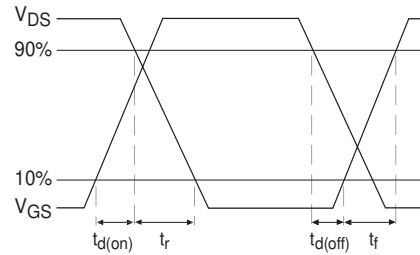


**Fig 8.** Maximum Safe Operating Area

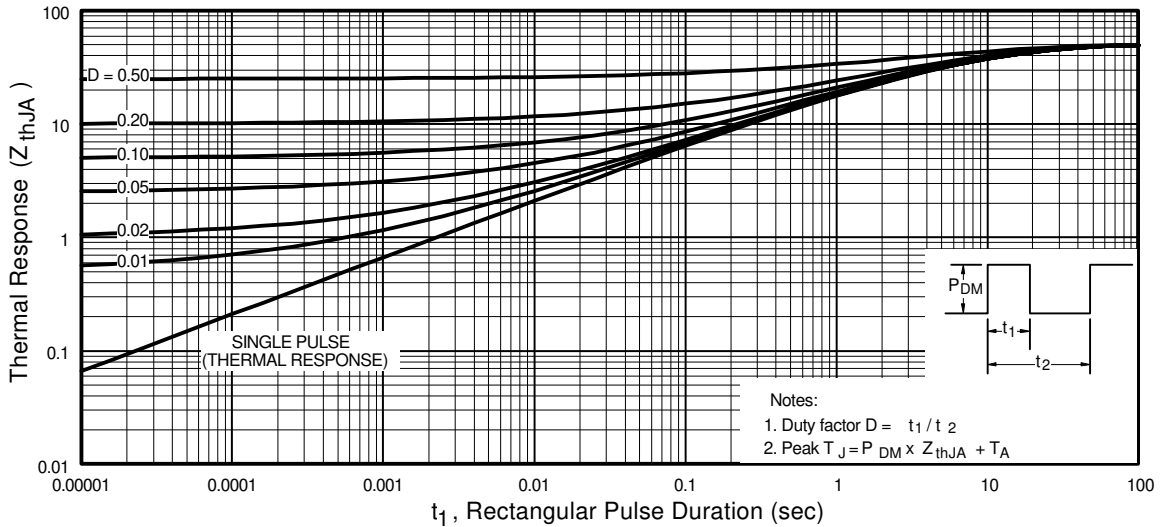
**Fig 6.** On-Resistance Vs. Drain Current



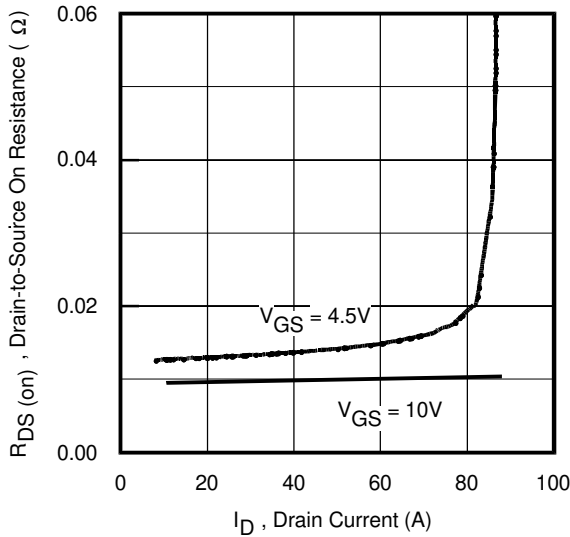
**Fig 10a.** Switching Time Test Circuit



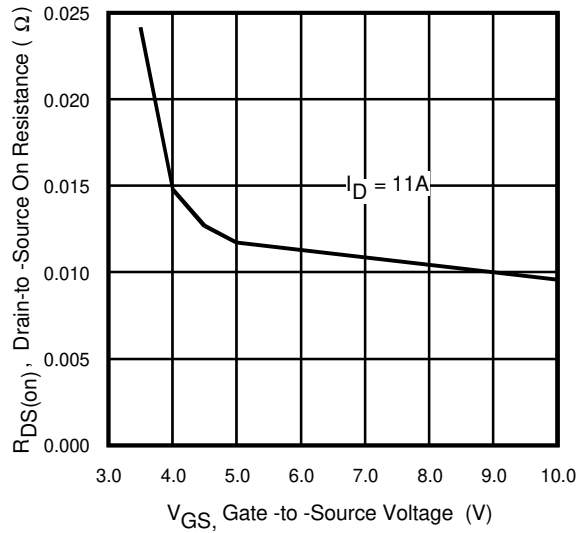
**Fig 10b.** Switching Time Waveforms



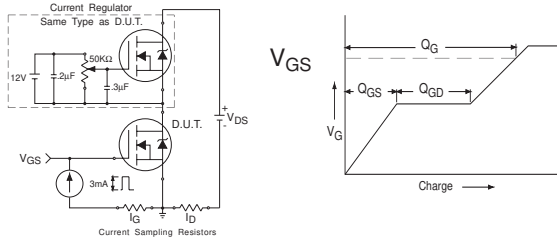
**Fig 10.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



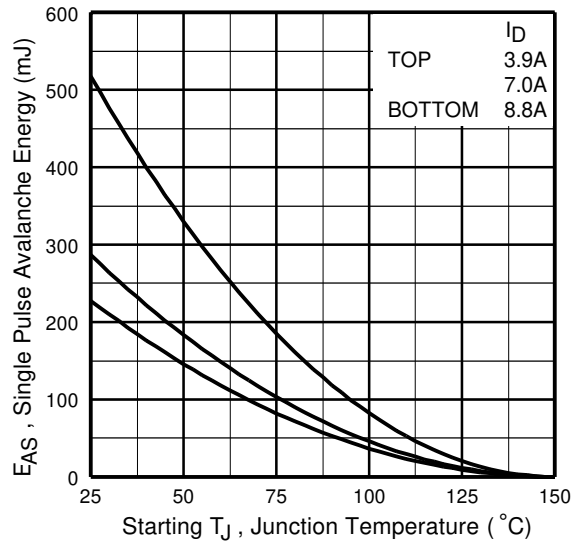
**Fig 12.** On-Resistance Vs. Drain Current



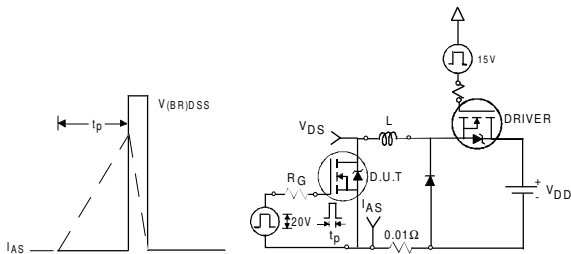
**Fig 13.** On-Resistance Vs. Gate Voltage



**Fig 13a&b.** Basic Gate Charge Test Circuit and Waveform

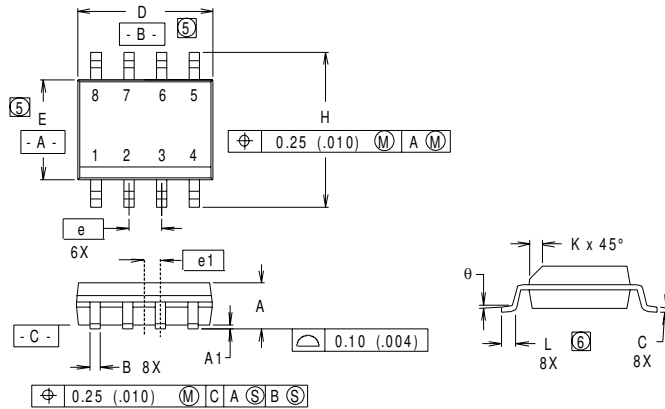


**Fig 14c.** Maximum Avalanche Energy Vs. Drain Current



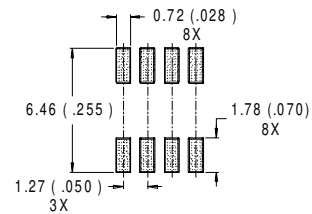
**Fig 14a&b.** Unclamped Inductive Test circuit and Waveforms

## SO-8 Package Details



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
B	.014	.018	0.36	0.46
C	.0075	.0098	0.19	0.25
D	.189	.196	4.80	4.98
E	.150	.157	3.81	3.99
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.011	.019	0.28	0.48
L	0.16	.050	0.41	1.27
θ	0°	8°	0°	8°

**RECOMMENDED FOOTPRINT**

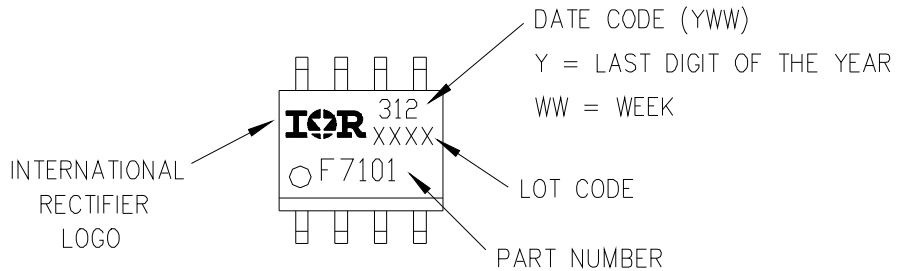


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS  
MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.006).
- ⑥ DIMENSIONS IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE..

## SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101

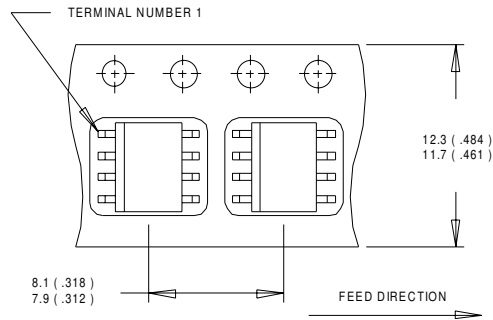




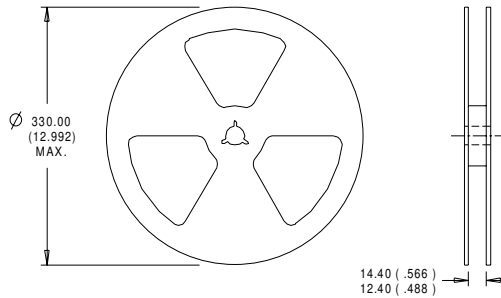
# IRF7466

International  
**IR** Rectifier

## SO-8 Tape and Reel



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 5.9\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 8.8\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ When mounted on 1 inch square copper board,  $t < 10$  sec

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Industrial market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
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